

1985 Spring Meeting Preview



April 15-18, 1985

Golden Gateway Holiday Inn
San Francisco, California

Twice the coverage...twice the attendance of the 1984 meeting projected

The Society's second Spring Meeting is rapidly shaping up under the management of Meeting Chairpersons A. W. Johnson, S. M. Kelso, and K. S. SreeHarsha. They report that seven focused symposia plus the popular Symposium for the Non-Specialist (Symposium X) will include approximately 375 papers representing the work of nearly 1,000 researchers. This amounts to nearly twice the breadth and participation of the highly successful first Spring Meeting held last year in Albuquerque, New Mexico.

The Spring Meeting, which was instituted as an extension of the popular Fall Meeting series in Boston, offers researchers from

the West Coast of the United States and East Asia a convenient annual venue for review of the state of the art in the most active fields of basic materials research. The importance of the MRS-style interdisciplinary approach to materials research is evidence by the Meeting's expanded technical scope and participation by hundreds of the most notable authorities in the field. MRS members — from the East and the West — are encouraged to review the up-coming Spring Meeting program and register by **March 20, 1985**, to take advantage of the special pre-registration fee. See the registration and housing reservation forms in this issue.

See the following brief descriptions of the symposia and also see the complete list of speakers in the Preliminary Program booklet.

REGISTER EARLY

Symposium A: Ion Beam Processes in Advanced Electronic Materials and Device Technology

April 15-17

Symposium Organizers: F. H. Eisen, Rockwell International
T. W. Sigmon, Stanford Electronics Laboratory
B. R. Appleton, Oak Ridge National Laboratory

The 59 papers will illustrate the increasing importance of ion beam processing in the fabrication of new semiconductor devices and integrated circuits. Topics will include: focused beams; shallow junctions, channeling tails, and amorphous layer regrowth; ion beam mixing, modification, and adhesion in metal/insulator/semiconductor systems; high dose rate and high energy implantation effects; implantation in compound semiconductor materials and devices; buried insulating layers, SOS and SOI; practical machine and implant considerations; and transient thermal annealing.

Invited speakers include: J. F. Gibbons, Stanford Electronics Laboratory; J. W. Mayer, Cornell University; T. E. Seidel, AT&T Bell Laboratories; B. G. Streetman, University of Texas; K. Gamo, Osaka University; G. C. Farlow, Oak Ridge National Laboratory; T. Venkatesan, Bell Communications Research; J. S. Williams,

Royal Melbourne Institute of Technology; D. E. Davies, Rome Air Development Center; and G. Ryding, Eaton Corporation.

Symposium Support: Division of Materials Science, Office of Basic Energy Sciences, U. S. Department of Energy; National Electrostatics Corporation; and Rockwell International.

Proceedings of this symposium will be published.

Symposium B: Microscopic Identification of Electronic Defects in Semiconductors

April 15-18

Symposium Organizers: Noble M. Johnson, Xerox Palo Alto Research Center
Stephen G. Bishop, Naval Research Laboratory
George D. Watkins, Lehigh University

Experimental and theoretical issues of establishing the microscopic identity of electronic defects in elemental and compound semiconductors will be explored in 82 papers. Emphasis will be on the role of theory; EL₂ and As_{C₃} antisite in GaAs; Group IV semiconductors/thermal donors; compound semiconductors; experimental techniques; and Group IV semiconductor interfaces.